

Triacs

Silicon Bidirectional Triode Thyristors

... designed primarily for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading
- Gate Triggering Guaranteed in Three Modes (MAC229 Series) or Four Modes (MAC229A Series)

MAC229 Series*

MAC229A Series*

*Motorola preferred devices

TRIACs
8 AMPERES RMS
200 thru 800 VOLTS



CASE 221A-04
 (TO-220AB)
 STYLE 4

3

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage, Note 1 (T _J = -40 to 110°C 1/2 Sine wave 50 to 60 Hz, Gate Open)	V _{DRM}		Volts
MAC229-4, MAC229A4		200	
MAC229-6, MAC229A6		400	
MAC229-8, MAC229A8		600	
MAC229-10, MAC229A10		800	
On-State RMS Current (T _C = 80°C) Full Cycle Sine Wave 50 to 60 Hz	I _{T(RMS)}	8	Amps
Peak Non-Repetitive Surge Current (One Full Cycle 60 Hz, T _J = 110°C)	I _{TSM}	80	Amps
Circuit Fusing (t = 8.3 ms)	I ² t	26	A ² s
Peak Gate Current (t ≤ 2 μs)	I _{GM}	±2	Amps
Peak Gate Voltage (t ≤ 2 μs)	V _{GM}	±10	Volts
Peak Gate Power (t ≤ 2 μs)	P _{GM}	20	Watts
Average Gate Power (T _C = 80°C, t ≤ 8.3 ms)	P _{G(AV)}	0.5	Watts
Operating Junction Temperature Range	T _J	-40 to 110	°C
Storage Temperature Range	T _{stg}	-40 to 150	°C
Mounting Torque		8	in. lb.

Note 1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded. (cont.)

MAC229 Series • MAC229A Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ and either polarity of MT2 to MT1 voltage unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Blocking Current, Note 1 ($V_D = \text{Rated } V_{DRM}$, Gate Open) $T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$	I_{DRM}	—	—	10 2	μA mA
Peak On-State Voltage ($I_{TM} = 11 \text{ A Peak}$, Pulse Width $\leq 2 \text{ ms}$, Duty Cycle $\leq 2\%$)	V_{TM}	—	—	1.8	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}$, $R_L = 100 \Omega$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	I_{GT}	—	—	10 15	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V}$, $R_L = 100 \Omega$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY ($V_D = \text{Rated } V_{DRM}$, $T_C = 110^\circ\text{C}$, $R_L = 10 \text{ k}$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-); MT2(-), G(+) "A" SUFFIX ONLY	V_{GT}	—	—	2 2.5	Volts
Holding Current ($V_D = 12 \text{ Vdc}$, $I_{TM} = 200 \text{ mA}$, Gate Open)	I_H	—	—	15	mA
Gate-Controlled Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 16 \text{ A Peak}$, $I_G = 30 \text{ mA}$)	t_{gt}	—	1.5	—	μs
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Waveform, $T_C = 110^\circ\text{C}$)	dv/dt	—	25	—	$\text{V}/\mu\text{s}$
Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11.3 \text{ A}$, Commutating $di/dt = 4.1 \text{ A/ms}$, Gate Unenergized, $T_C = 80^\circ\text{C}$)	$dv/dt(c)$	—	5	—	$\text{V}/\mu\text{s}$

Note 1. Ratings apply for open gate conditions. Devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage.

